

参数表

2CL10KV-100mA 系列高压高频二极管采用高可靠性的台面结构及扩散工艺，环氧树脂真空灌注密封封装。

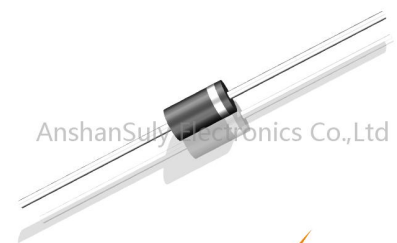
2CL10KV-100mA Series High voltage rectifier diode adopts high reliable mesa structure and diffusion craftwork, epoxy resin molded in a compact structure.

▼ 产品特点 Feature

- ❖ 雪崩电压击穿保护特性 **Avalanche Characteristic**
- ❖ 优异的抗浪涌电流冲击特性 **Excellent surge current resistance**
- ❖ 高速开关响应特性 **High speed switch response characteristics**
- ❖ 采用新型环氧树脂真空封装技术，表面具有抗腐蚀性
Epoxy resin molded in vacuum, have anticorrosion in the surface
- ❖ 工作结温 -50℃—+175℃ **T_j:50℃—+175℃**
- ❖ 特殊耐高温性能芯片，可承受严酷恶劣的使用条件
Special high temperature resistant chip that can withstand harsh working conditions

▼ 产品 2D 图示

Graphical Representation



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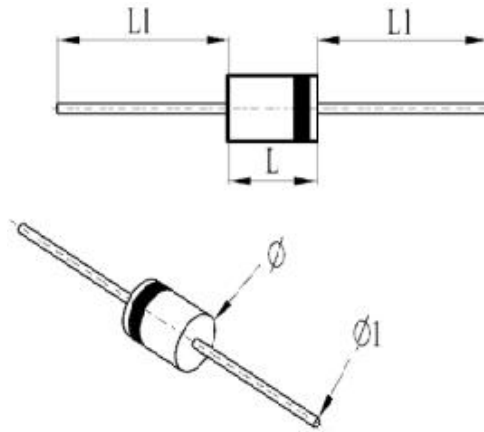


	参数名称 Item	符号 Symbol	单位 Unit	测试条件 Conditions	数值 Rating
绝对值 (绝对最大值) Absolute Maximum Ratings	反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	KV	Ta=25℃ I _R =2.0μA	10
	反向工作峰值电压) Peak Working Revere Voltage	V_{RWM}	KV	Ta=25℃ I _R =2.0μA	10
	正向平均电流 Average Forward Current	$I_{F(AV)}$	mA	正弦半波 50Hz, 电阻负载, T _{break} =50℃ (50Hz Half-sine Wave , Resistance load @T _{break} =50℃)	100
	反向恢复时间 Reverse Recovery Time	trr	nS		--
	正向(不重复)浪涌电流 Surge Forward Current	I_{FSM}	A	正弦半波持续时间 0.01S 50Hz 0.01S @ Half-Sine wave 50Hz	10
	工作环境温度 Operating Ambient Temperature	T _j	℃		-55~+150
	存储温度 Storage Temperature	T _{stg}	℃		-40~+125
电特性 Electrical Characteristics	正向峰值电压 Forward Peak Voltage	V_{FM}	V	@ Ta=25℃ I _f =100mA	12
	反向峰值电流 Peak Reverse Current	I_{RRM1}	μA	@ Ta=25℃ V _{RM} =V _{RRM}	2.0
		I_{RRM2}	μA	@ Ta=100℃ V _{RM} =V _{RRM}	20.0

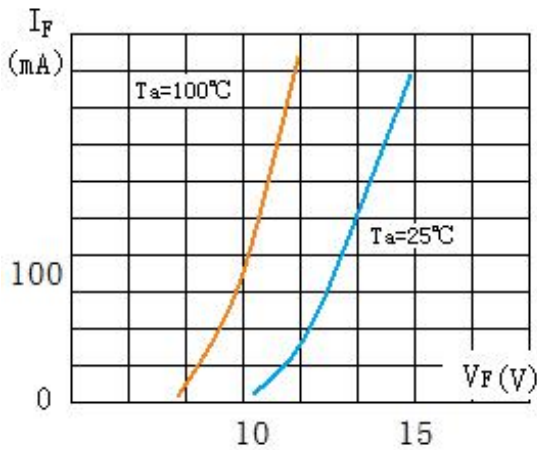
▼ 外形尺寸图示 Outline Drawings

(单位：毫米 mm)

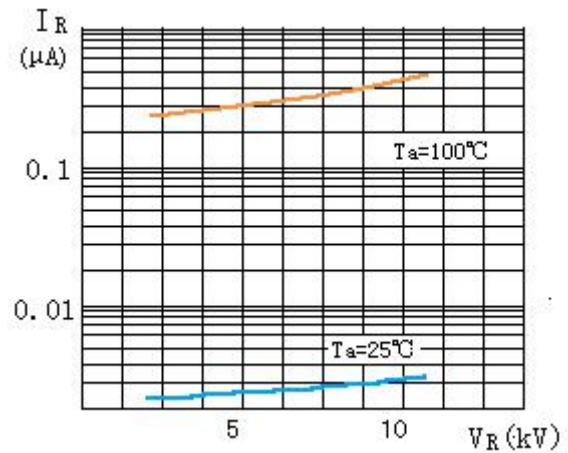
尺寸/图号	直径 (Φ)	长 (L)	线径 (Φ1)	线长 (L1)
Fig①	5	9	1.2	>20
Fig②	4.5	15	1.2	>20



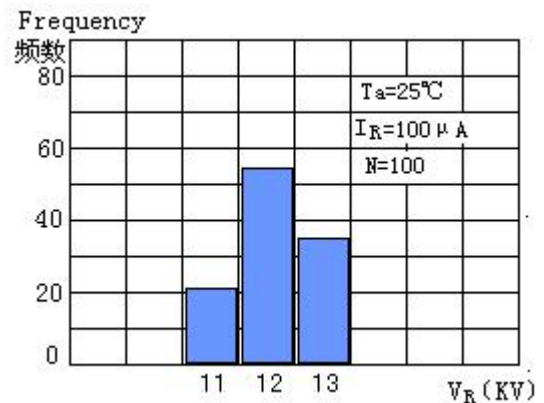
▼ 特性曲线图 Characteristic Curve



正向特性曲线 (2CL10KV-100mA)
Forward Characteristics



反向特性曲线 (2CL10KV-100mA)
Reverse Characteristics



反向雪崩电压分布 (2CL10KV-100mA)
Avalanche Breakdown Voltage